

ABSTRACT OF THE DISCLOSURE

A method of forming memory circuitry sequentially includes forming a plurality of metal interconnect lines over a semiconductive substrate. A plurality of memory cell storage devices comprising voltage or current controlled resistance settable semiconductive material are then formed. In one implementation, a method of forming integrated circuitry includes forming a metal interconnect line over a semiconductive substrate. A device comprising two metal comprising electrodes separated by a voltage or current controlled resistance settable semiconductive material is formed. The resistance settable semiconductive material is formed after forming the metal interconnect line.

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